TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSIV)

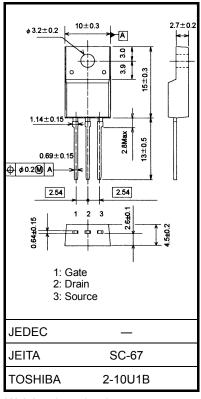
2SK3564

Switching Regulator Applications

- Low drain-source ON resistance: R_{DS} (ON) = 3.7 Ω (typ.)
- High forward transfer admittance: |Y_{fs}| = 2.6 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (V_{DS} = 720 V)
- Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit |
|--|------------------------------|------------------|---------|------|
| Drain-source voltage | | V _{DSS} | 900 | V |
| Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$) | | V _{DGR} | 900 | V |
| Gate-source voltage | | V _{GSS} | ±30 | V |
| Drain current | DC (Note 1) | ۱ _D | 3 | |
| | Pulse (t = 1 ms) (Note 1) | I _{DP} | 9 | A |
| Drain power dissipation (Tc = 25° C) | | PD | 40 | W |
| Single pulse avalanche energy (Note 2) | | E _{AS} | 408 | mJ |
| Avalanche current | | I _{AR} | 3 | А |
| Repetitive avalanche energy (Note 3) | | E _{AR} | 4.0 | mJ |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature range | | T _{stg} | -55~150 | °C |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

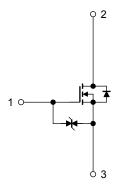
| Characteristics | Symbol | Max | Unit |
|--|------------------------|-------|------|
| Thermal resistance, channel to case | R _{th (ch-c)} | 3.125 | °C/W |
| Thermal resistance, channel to ambient | R _{th (ch-a)} | 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}, \text{ L} = 83 \text{ mH}, \text{ I}_{AR} = 3.0 \text{ A}, \text{ R}_{G} = 25 \Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



Unit: mm

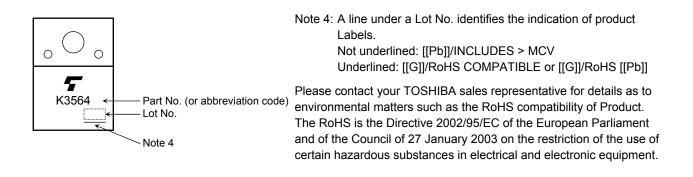
Electrical Characteristics (Ta = 25°C)

| Char | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|------------------------------|----------------|----------------------|---|------|------|-----|------|
| Gate leakage current | | I _{GSS} | $V_{GS}=\pm 25~V,~V_{DS}=0~V$ | _ | | ±10 | μA |
| Gate-source brea | akdown voltage | V (BR) GSS | $I_G=\pm 10~\mu A,~V_{DS}=0~V$ | ±30 | | _ | V |
| Drain cut-off curr | ent | IDSS | $V_{DS} = 720 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$ | | | 100 | μA |
| Drain-source bre | akdown voltage | V (BR) DSS | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ | 900 | | | V |
| Gate threshold ve | oltage | V _{th} | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$ | 2.0 | — | 4.0 | V |
| Drain-source ON | resistance | R _{DS (ON)} | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1.5 \text{ A}$ | | 3.7 | 4.3 | Ω |
| Forward transfer | admittance | Y _{fs} | $V_{DS} = 20 \text{ V}, \text{ I}_{D} = 1.5 \text{ A}$ | 0.65 | 2.6 | — | S |
| Input capacitance | | C _{iss} | V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz | | 700 | _ | pF |
| Reverse transfer capacitance | | C _{rss} | | | 15 | _ | |
| Output capacitance | | C _{oss} | | | 75 | | |
| Switching time | Rise time | tr | V_{GS} $0 V$ V_{GS} $0 V$ V_{GS} $0 V$ V_{GS} $0 V$ V_{CD} $R_{L} =$ 133Ω $V_{DD} \simeq 200 V$ | _ | 20 | _ | |
| | Turn-on time | t _{on} | | _ | 60 | — | |
| | Fall time | t _f | | _ | 35 | _ | ns |
| | Turn-off time | t _{off} | Duty \leq 1%, t _w = 10 μ s | | 125 | _ | |
| Total gate charge | | Qg | | _ | 17 | | |
| Gate-source charge | | Q _{gs} | $V_{DD} \simeq 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$ | _ | 10 | | nC |
| Gate-drain charge | | Q _{gd} |] | | 7 | | |

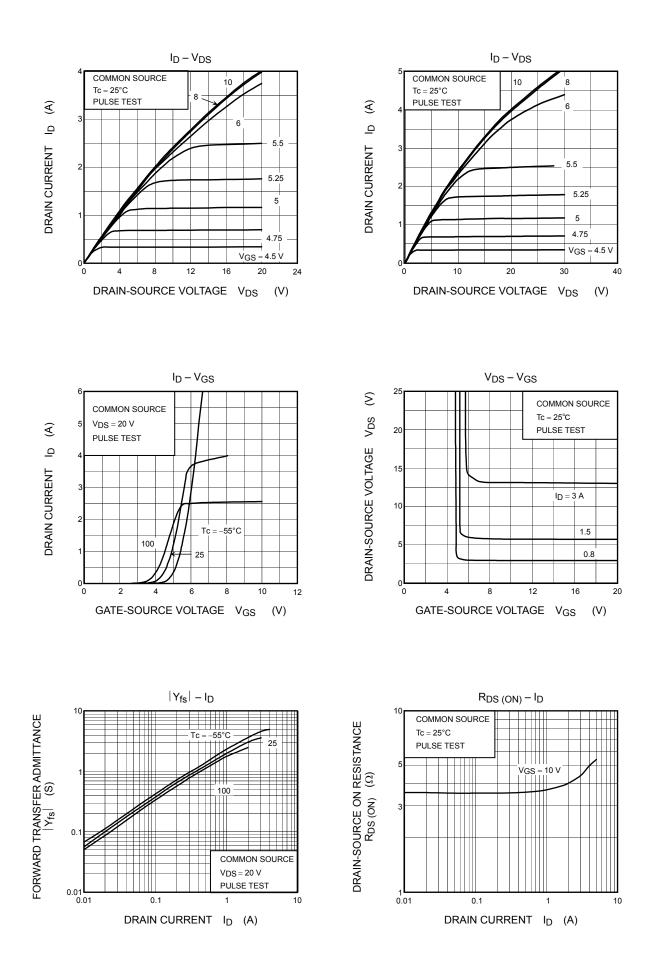
Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I _{DR} | — | _ | _ | 3 | А |
| Pulse drain reverse current (Note 1) | I _{DRP} | — | _ | _ | 9 | А |
| Forward voltage (diode) | V _{DSF} | I _{DR} = 3 A, V _{GS} = 0 V | _ | _ | -1.9 | V |
| Reverse recovery time | t _{rr} | $I_{DR} = 3 \text{ A}, V_{GS} = 0 \text{ V},$ | _ | 850 | _ | ns |
| Reverse recovery charge | Q _{rr} | dl _{DR} /dt = 100 A/μs | _ | 4.7 | _ | μC |

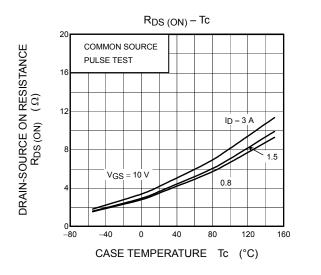
Marking

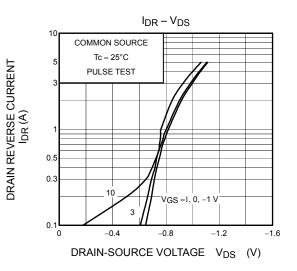


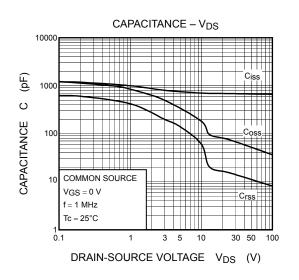
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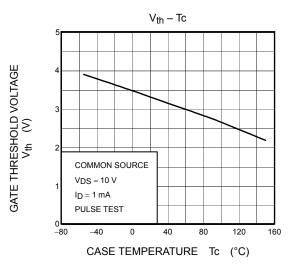


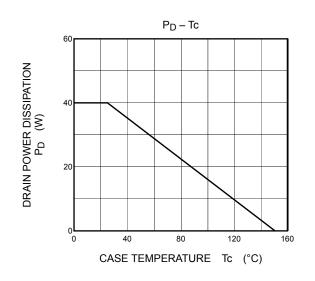
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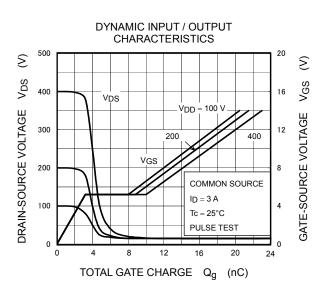


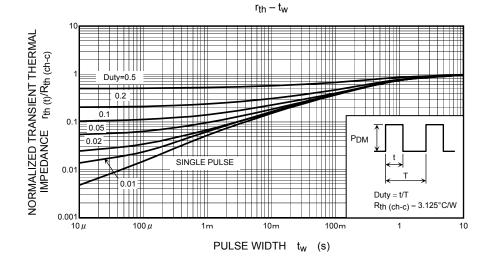


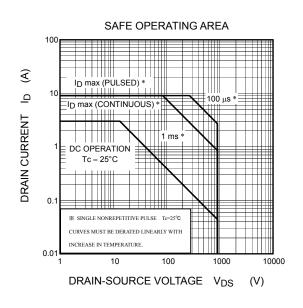


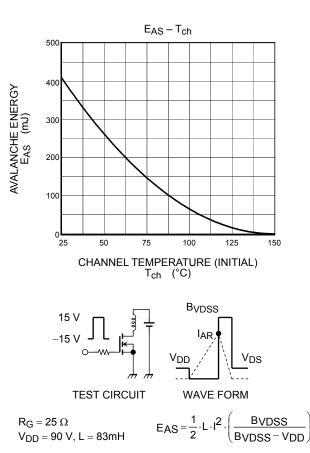












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